

# **isc Silicon NPN Power Transistor**

## 2N5202

#### **DESCRIPTION**

- Collector-emitter sustaining voltage V<sub>CEO(SUS)</sub>= 90V(Min)
- · High saturation voltage
- · Wide area of safe operation
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### **APPLICATIONS**

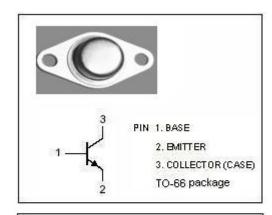
 Designed for use in high-current, high-speed switching circuits such as:low-distortion power amplifiers,oscillators, switching regulators, series regulators, converters, and inverters.

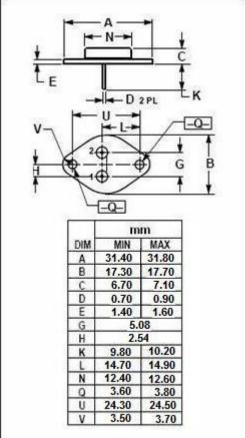
## ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	100	V
V <sub>CEO(SUS)</sub>	Collector-Emitter Voltage	50	V
V <sub>CER(SUS)</sub>	Collector-Emitter Voltage R <sub>BE</sub> = 50 Ω 75		V
V <sub>EBO</sub>	Emitter-Base Voltage 6		V
Ic	Collector Current-Continuous	4	Α
I <sub>CM</sub>	Collector Current-Peak 5		А
I <sub>B</sub>	Base Current-Continuous	2	А
P <sub>D</sub>	Total Power Dissipation@Tc=25°C	35	W
TJ	Junction Temperature	-65~200	$^{\circ}$ C
T <sub>stg</sub>	Storage Temperature	-65~235	$^{\circ}$

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance,Junction to Case	5.0	°C/W







### isc Silicon NPN Power Transistor

2N5202

#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 200mA; I <sub>B</sub> = 0	50		V
V <sub>CER(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 200mA; I <sub>B</sub> = 0	75		V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 4A; I <sub>B</sub> = 0.4A		1.2	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	Ic= 4A; I <sub>B</sub> = 0.4A		2.0	V
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = 70V; I <sub>B</sub> = 0		10	mA
ІЕВО	Emitter Cutoff Current	V <sub>EB</sub> = 6V; I <sub>C</sub> = 0		10	mA
h <sub>FE1</sub>	DC Current Gain	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 10V	6		
h <sub>FE2</sub>	DC Current Gain	I <sub>C</sub> = 4A; V <sub>CE</sub> = 1.2V	10	100	

#### **Notice:**

ISC reserves the rights to make changes of the content herein the datasheet at any time without notification. The information contained herein is presented only as a guide for the applications of our products.

ISC products are intended for usage in general electronic equipment. The products are not designed for use in equipment which require specialized quality and/or reliability, or in equipment which could have applications in hazardous environments, aerospace industry, or medical field. Please contact us if you intend our products to be used in these special applications.

ISC makes no warranty or guarantee regarding the suitability of its products for any particular purpose, nor does ISC assume any liability arising from the application or use of any products, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages.